

Features

Type	V _{DSS}	R _{DS(on)}	I _D
STB185N10F3	100 V	4.5 mΩ	120 A ⁽¹⁾
STP185N10F3	100 V	4.8 mΩ	120 A ⁽¹⁾

1. Value limited by wire bonding

- Ultra low on-resistance
- 100% avalanche tested

Application

- Switching application
 - Automotive

Description

This n-channel enhancement mode Power MOSFET is the latest refinement of STMicroelectronics unique "single feature size" strip-based process with less critical alignment steps and therefore a remarkable manufacturing reproducibility. The resulting transistor shows extremely high packing density for low on-resistance, rugged avalanche characteristics and low gate charge.

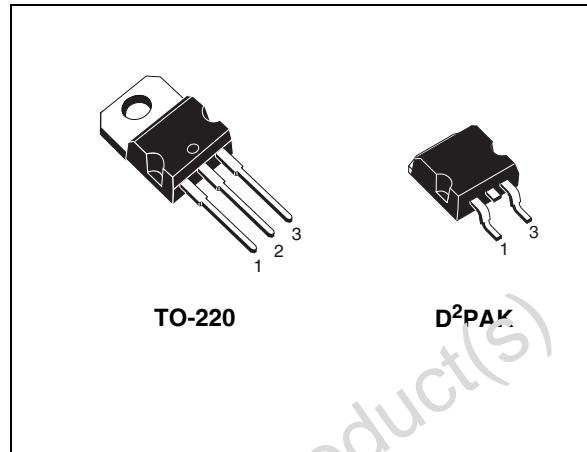


Figure 1. Internal schematic diagram

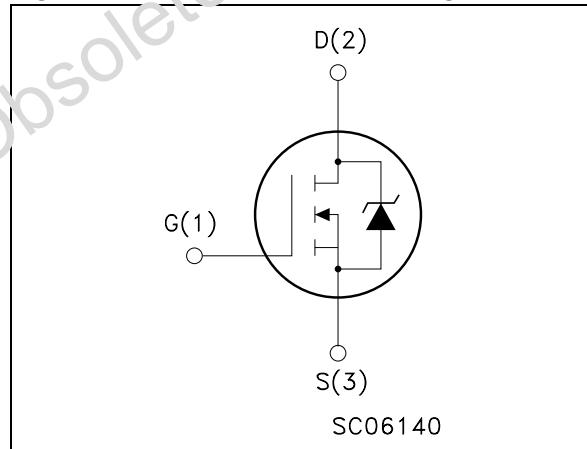


Table 1 Device summary

Order codes	Marking	Package	Packaging
STB185N10F3	185N10F3	D ² PAK	Tape and reel
STP185N10F3	185N10F3	TO-220	Tube

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Obsolete Product(s) - Obsolete Product(s)

1 Electrical ratings

Table 2. Absolute maximum ratings

Symbol	Parameter	Value	Unit
V_{DS}	Drain-source voltage ($V_{GS}=0$)	100	V
V_{GS}	Gate-source voltage	± 20	V
$I_D^{(1)}$	Drain current (continuous) at $T_C = 25^\circ C$	120	A
$I_D^{(1)}$	Drain current (continuous) at $T_C=100^\circ C$	120	A
$I_{DM}^{(2)}$	Drain current (pulsed)	480	A
P_{TOT}	Total dissipation at $T_C = 25^\circ C$	300	W
	Derating factor	2.0	W/ $^\circ C$
dv/dt	Peak diode recovery voltage slope	TBD	V/ns
$E_{AS}^{(3)}$	Single pulse avalanche energy	TBD	mJ
T_j T_{stg}	Operating junction temperature storage temperature	-55 To 175	$^\circ C$

1. Current limited by package.
2. Pulse width limited by safe operating area.
3. Starting $T_j=25^\circ C$, $I_D=60 A$, $V_{DD}=40 V$

Table 3. Thermal data

Symbol	Parameter	TO-220	D ² PAK	Unit
R _{thj-case}	Thermal resistance junction-case	0.5		$^\circ C/W$
R _{thj-a}	Thermal resistance junction-ambient max	62.5	--	$^\circ C/W$
R _{thj-pcb⁽¹⁾}	Thermal resistance junction-ambient max	--	35	$^\circ C/W$
T _I	Maximum lead temperature for soldering purpose	300	--	$^\circ C$

1. When mounted on FR-4 board, on 1inch², 2oz Cu.

2 Electrical characteristics

($T_{CASE}=25^\circ\text{C}$ unless otherwise specified)

Table 4. On/off states

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage	$I_D = 250 \mu\text{A}, V_{GS} = 0$	100			V
I_{DSS}	Zero gate voltage drain current ($V_{GS} = 0$)	$V_{DS} = \text{max rating}, V_{DS} = \text{max rating, } @125^\circ\text{C}$			10 100	μA μA
I_{GSS}	Gate body leakage current ($V_{DS} = 0$)	$V_{GS} = \pm 20 \text{ V}$			± 200	nA
$V_{GS(\text{th})}$	Gate threshold voltage	$V_{DS} = V_{GS}, I_D = 250 \mu\text{A}$	2		4	V
$R_{DS(\text{on})}$	Static drain-source on resistance	$V_{GS} = 10 \text{ V}, I_D = 60 \text{ A}$ D ² PAK TO-220			4.5 4.8	$\text{m}\Omega$ $\text{m}\Omega$

Table 5. Dynamic

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
C_{iss}	Input capacitance			TBD		pF
C_{oss}	Output capacitance			TBD		pF
C_{rss}	Reverse transfer capacitance	$V_{DS} = 25 \text{ V}, f = 1 \text{ MHz}, V_{GS} = 0$		TBD		pF
Q_g	Total gate charge	$V_{DD} = 80 \text{ V}, I_D = 120 \text{ A}, V_{GS} = 10 \text{ V}$		100	TBD	nC
Q_{gs}	Gate-source charge	(see Figure 3)		TBD		nC
Q_{gd}	Gate-drain charge			TBD		nC

Table 6. Dynamic

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on delay time			TBD		ns
t_r	Rise time			TBD		ns
$t_{d(off)}$	Turn-off delay time			TBD		ns
t_f	Fall time	$V_{DD} = 50 \text{ V}, I_D = 60 \text{ A}$ $R_G = 4.7 \Omega, V_{GS} = 10 \text{ V}$ (see Figure 2 , Figure 7)		TBD		ns

Table 7. Source drain diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
I_{SD}	Source-drain current				120	A
$I_{SDM}^{(1)}$	Source-drain current (pulsed)				480	A
$V_{SD}^{(2)}$	Forward on voltage	$I_{SD}=120\text{ A}, V_{GS}=0$			1.5	V
t_{rr}	Reverse recovery time	$I_{SD}=120\text{ A},$ $di/dt = 100\text{ A}/\mu\text{s},$ $V_{DD}=30\text{ V}, T_j=150^\circ\text{C}$		TBD		ns
Q_{rr}	Reverse recovery charge			TBD		μC
I_{RRM}	Reverse recovery current (see <i>Figure 4</i>)			TBD		A

1. Pulse width limited by safe operating area
2. Pulsed: pulse duration = 300 μs , duty cycle 1.5%

3 Test circuit

Figure 2. Switching times test circuit for resistive load

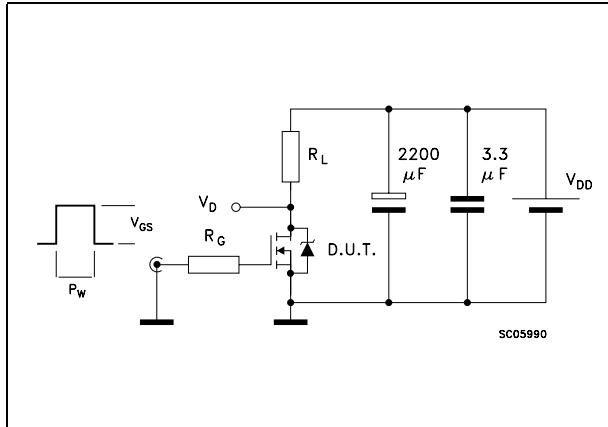


Figure 3. Gate charge test circuit

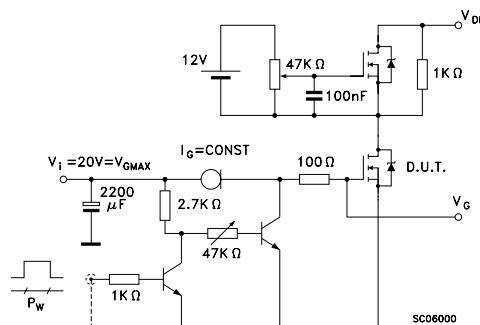


Figure 4. Test circuit for inductive load switching and diode recovery times

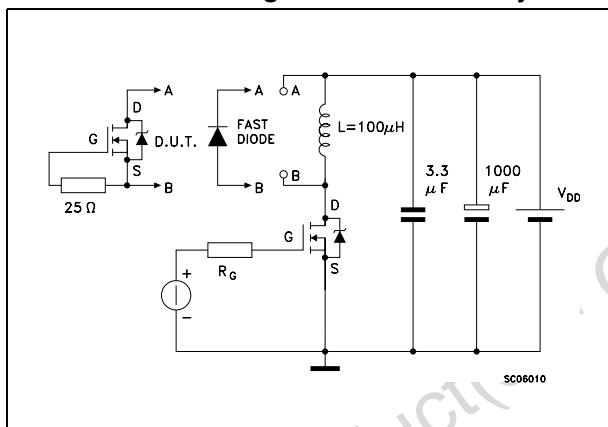


Figure 5. Unclamped inductive load test circuit

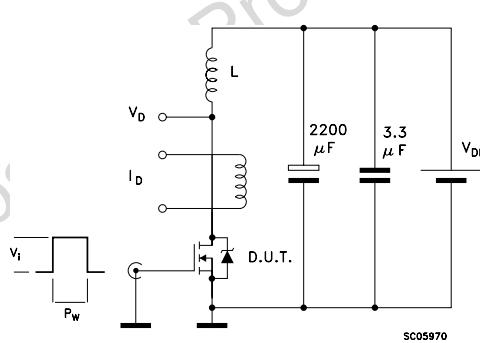


Figure 6. Unclamped inductive waveform

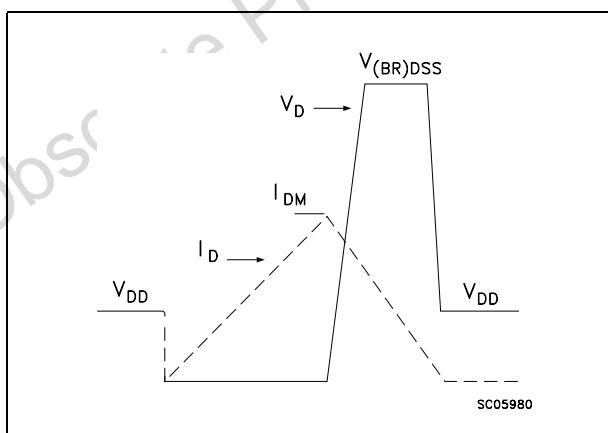
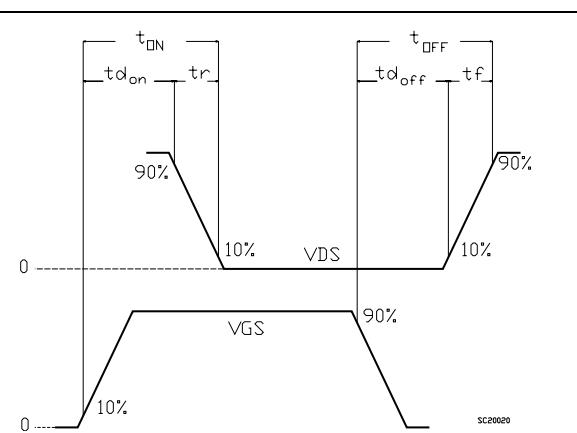


Figure 7. Switching time waveform



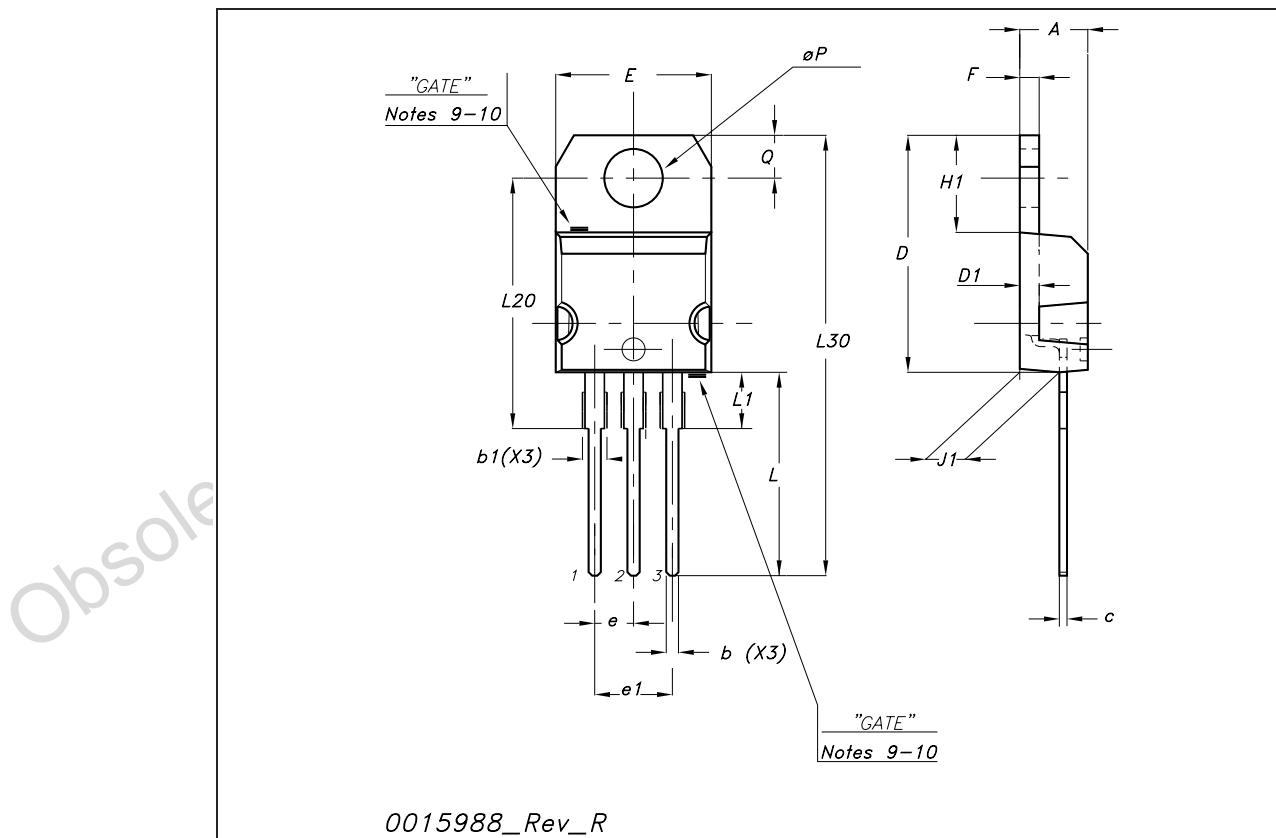
4 Package mechanical data

In order to meet environmental requirements, ST offers these devices in ECOPACK® packages. These packages have a Lead-free second level interconnect. The category of second level interconnect is marked on the package and on the inner box label, in compliance with JEDEC Standard JESD97. The maximum ratings related to soldering conditions are also marked on the inner box label. ECOPACK is an ST trademark. ECOPACK specifications are available at: www.st.com

Obsolete Product(s) - Obsolete Product(s)

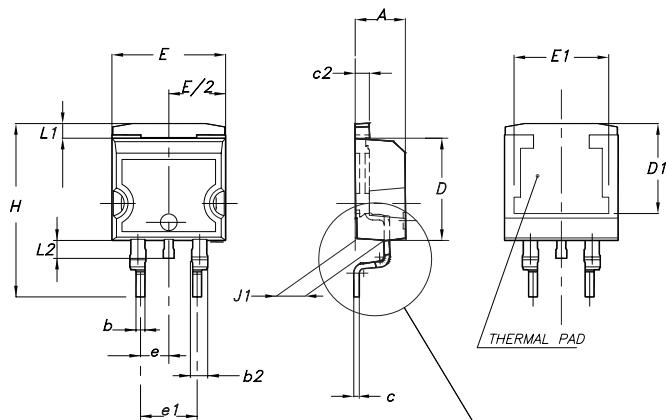
TO-220 mechanical data

Dim	mm			inch		
	Min	Typ	Max	Min	Typ	Max
A	4.40		4.60	0.173		0.181
b	0.61		0.88	0.024		0.034
b1	1.14		1.70	0.044		0.066
c	0.48		0.70	0.019		0.027
D	15.25		15.75	0.6		0.62
D1		1.27			0.050	
E	10		10.40	0.393		0.409
e	2.40		2.70	0.094		0.106
e1	4.95		5.15	0.194		0.202
F	1.23		1.32	0.048		0.051
H1	6.20		6.60	0.244		0.256
J1	2.40		2.72	0.094		0.107
L	13		14	0.511		0.551
L1	3.50		3.93	0.137		0.154
L20		16.40			0.645	
L30		28.90			1.137	
$\emptyset P$	3.75		3.85	0.147		0.151
Q	2.65		2.95	0.104		0.116

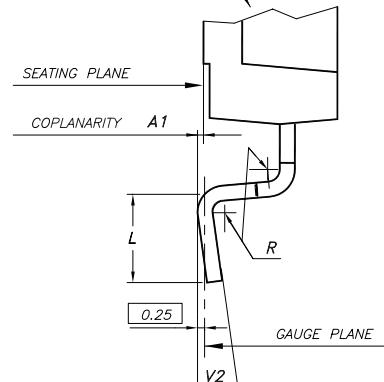


D²PAK (TO-263) mechanical data

Dim	mm			inch		
	Min	Typ	Max	Min	Typ	Max
A	4.40		4.60	0.173		0.181
A1	0.03		0.23	0.001		0.009
b	0.70		0.93	0.027		0.037
b2	1.14		1.70	0.045		0.067
c	0.45		0.60	0.017		0.024
c2	1.23		1.36	0.048		0.053
D	8.95		9.35	0.352		0.368
D1	7.50			0.295		
E	10		10.40	0.394		0.409
E1	8.50			0.334		
e		2.54			0.1	
e1	4.88		5.28	0.192		0.208
H	15		15.85	0.590		0.624
J1	2.49		2.69	0.099		0.106
L	2.29		2.79	0.090		0.110
L1	1.27		1.40	0.05		0.055
L2	1.30		1.75	0.051		0.069
R		0.4			0.016	
V2	0°		8°	0°		8°

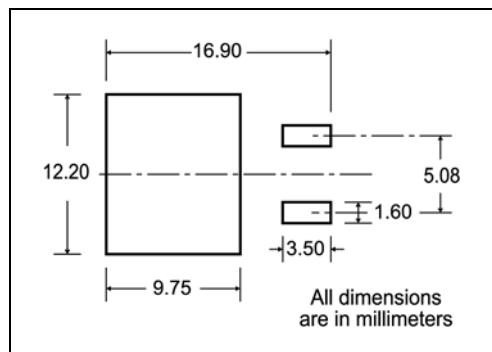


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5 Packaging mechanical data

D²PAK FOOTPRINT



TAPE AND REEL SHIPMENT

REEL MECHANICAL DATA				
DIM.	mm		inch	
	MIN.	MAX.	MIN.	MAX.
A		330		12.992
B	1.5		0.059	
C	12.8	13.2	0.504	0.520
D	20.2		0795	
G	24.4	26.4	0.960	1.039
N	100		3.937	
T		30.4		1.197
BASE QTY		BULK QTY		
1000		1000		

TAPE MECHANICAL DATA

DIM.	mm		inch	
	MIN.	MAX.	MIN.	MAX.
A0	10.5	10.7	0.413	0.421
B0	15.7	15.9	0.618	0.626
D	1.5	1.6	0.059	0.063
D1	1.59	1.61	0.062	0.063
E	1.65	1.85	0.065	0.073
F	11.4	11.6	0.449	0.456
K0	4.8	5.0	0.189	0.197
P0	3.9	4.1	0.153	0.161
P1	11.9	12.1	0.468	0.476
P2	1.9	2.1	0.075	0.082
R	50		1.574	
T	0.25	0.35	0.0098	0.0137
W	23.7	24.3	0.933	0.956

* on sales type

6 Revision history

Table 8. Document revision history

Date	Revision	Changes
01-Aug-2007	1	First version

Obsolete Product(s) - Obsolete Product(s)

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